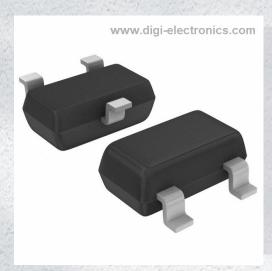


MUN2216T1G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MUN2216T1G-DG

Manufacturer onsemi

Manufacturer Product Number MUN2216T1G

Description TRANS PREBIAS NPN 50V 0.1A SC59

Detailed Description Pre-Biased Bipolar Transistor (BJT) NPN - Pre-Biase d 50 V 100 mA 338 mW Surface Mount SC-59



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MUN2216T1G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	4.7 kOhms
DC Current Gain (hFE) (Min) @ Ic, Vce:	Vce Saturation (Max) @ lb, Ic:
160 @ 5mA, 10V	250mV @ 1mA, 10mA
Current - Collector Cutoff (Max):	Power - Max:
500nA	338 mW
Mounting Type:	Package / Case:
Surface Mount	TO-236-3, SC-59, SOT-23-3
Supplier Device Package:	Base Product Number:
SC-59	MUN2216

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



Digital Transistors (BRT) $R1 = 4.7 k\Omega$, $R2 = \infty k\Omega$

NPN Transistors with Monolithic Bias Resistor Network

MUN2216, MMUN2216L, MUN5216, DTC143TE, DTC143TM3, NSBC143TF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

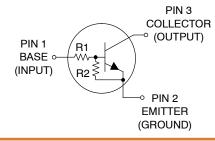
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

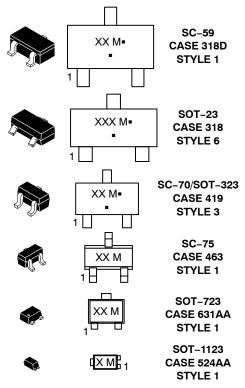
Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current - Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	30	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code = Date Code* = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been DISCONTINUED. Please refer to the table on page 2.

1

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2216T1G, SMUN2216T1G	8F	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2216LT1G, SMMUN2216LT1G	A8F	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMUN2216LT3G	A8F	SOT-23 (Pb-Free)	10000 / Tape & Reel
MUN5216T1G, NSVMUN5216T1G	8F	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC143TET1G	8F	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC143TM3T5G	8F	SOT-723 (Pb-Free)	8000 / Tape & Reel

DISCONTINUED (Note 1)

NSBC143TF3T5G	F (180°)	SOT-1123 (Pb-Free)	8000 / Tape & Reel
		(1 D-1 166)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

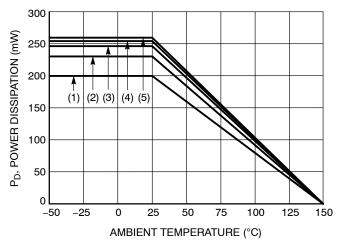


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

^{*} (xx°) = Degree rotation in the clockwise direction.

Table 2. THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTER	ISTICS (SC-59) (MUN2216)			
Total Device Dissipation		P _D		
$T_A = 25^{\circ}C$	(Note 2)		230	mW
	(Note 3)		338	
Derate above 25°C	(Note 2)		1.8	mW/°C
	(Note 3)		2.7	
Thermal Resistance,	(Note 2)	$R_{ hetaJA}$	540	°C/W
Junction to Ambient	(Note 3)		370	
Thermal Resistance,	(Note 2)	$R_{ hetaJL}$	264	°C/W
Junction to Lead	(Note 3)	1.000	287	-,
Junction and Storage Tem	perature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTER	ISTICS (SOT-23) (MMUN2216L)	•		
Total Device Dissipation	, , , ,	P _D		
$T_A = 25^{\circ}C$	(Note 2)	ا ا	246	mW
1A = 23 G	(Note 3)		400	
Derate above 25°C	(Note 2)		2.0	mW/°C
	(Note 3)		3.2	,
Thermal Resistance,	(Note 1)	$R_{ hetaJA}$	508	°C/W
Junction to Ambient	(Note 3)	OUA.	311	
Thermal Resistance,	(Note 2)	$R_{ hetaJL}$	174	°C/W
Junction to Lead	(Note 3)	1-03E	208	-,
Junction and Storage Tem	perature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTER	ISTICS (SC-70/SOT-323) (MUN5216)	•	•	
Total Device Dissipation		P _D		
T _A = 25°C	(Note 2)		202	mW
7	(Note 3)		310	
Derate above 25°C	(Note 2)		1.6	mW/°C
	(Note 3)		2.5	
Thermal Resistance,	(Note 2)	$R_{ hetaJA}$	618	°C/W
Junction to Ambient	(Note 3)		403	
Thermal Resistance,	(Note 2)	$R_{ hetaJL}$	280	°C/W
Junction to Lead	(Note 3)	1.002	332	-,
Junction to Leau	(002	
		T _J , T _{stg}	-55 to +150	°C
Junction and Storage Tem	perature Range	T _J , T _{stg}		°C
Junction and Storage Tem		•		°C
Junction and Storage Tem THERMAL CHARACTER Total Device Dissipation	perature Range	T _J , T _{stg}		°C mW
Junction and Storage Tem THERMAL CHARACTER Total Device Dissipation T _A = 25°C	pperature Range ISTICS (SC-75) (DTC143TE) (Note 2) (Note 3)	•	-55 to +150	
Junction and Storage Tem THERMAL CHARACTER Total Device Dissipation	ISTICS (SC-75) (DTC143TE) (Note 2) (Note 3) (Note 2)	•	-55 to +150 200 300 1.6	
Junction and Storage Tem THERMAL CHARACTER Total Device Dissipation T _A = 25°C	pperature Range ISTICS (SC-75) (DTC143TE) (Note 2) (Note 3)	•	-55 to +150 200 300	mW
Junction and Storage Term THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}\text{C}$ Derate above 25°C	(Note 2) (Note 3) (Note 3) (Note 3) (Note 3)	•	-55 to +150 200 300 1.6	mW
Junction and Storage Tem THERMAL CHARACTER Total Device Dissipation T _A = 25°C	(Note 2) (Note 3) (Note 3)	P _D	-55 to +150 200 300 1.6 2.4	mW mW/°C
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation T _A = 25°C Derate above 25°C Thermal Resistance, Junction to Ambient	(Note 2) (Note 2) (Note 2) (Note 3) (Note 3) (Note 3) (Note 3)	P _D	-55 to +150 200 300 1.6 2.4 600	mW mW/°C
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C Thermal Resistance, Junction to Ambient Junction and Storage Terr	(Note 2) (Note 2) (Note 2) (Note 3) (Note 3) (Note 3) (Note 3)	P _D	-55 to +150 200 300 1.6 2.4 600 400	mW mW/°C °C/W
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C Thermal Resistance, Junction to Ambient Junction and Storage Terr	(Note 2) (Note 3) (Note 2) (Note 3) (Note 3) (Note 3) (Note 3) (Note 3) (Note 3) (Sometime of the state of th	P _D R ₀ JA T _J , T _{stg}	-55 to +150 200 300 1.6 2.4 600 400	mW mW/°C °C/W
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation T _A = 25°C Derate above 25°C Thermal Resistance, Junction to Ambient Junction and Storage Terr THERMAL CHARACTER	(Note 2) (Note 3) (Note 3) (Note 3) (Note 3) (Note 3)	P _D	-55 to +150 200 300 1.6 2.4 600 400	mW mW/°C °C/W
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation T _A = 25°C Derate above 25°C Thermal Resistance, Junction to Ambient Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation	(Note 2) (Note 3) (Note 2) (Note 3)	P _D R ₀ JA T _J , T _{stg}	-55 to +150 200 300 1.6 2.4 600 400 -55 to +150	mW mW/°C °C/W
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation T _A = 25°C Derate above 25°C Thermal Resistance, Junction to Ambient Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)	P _D R ₀ JA T _J , T _{stg}	-55 to +150 200 300 1.6 2.4 600 400 -55 to +150	mW mW/°C °C/W
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C Thermal Resistance, Junction to Ambient Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$	(Note 2) (Note 3) (Note 2) (Note 3)	P _D R ₀ JA T _J , T _{stg}	-55 to +150 200 300 1.6 2.4 600 400 -55 to +150	mW mW/°C °C/W °C
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C Thermal Resistance, Junction to Ambient Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)	P _D R _θ JA T _J , T _{stg}	-55 to +150 200 300 1.6 2.4 600 400 -55 to +150 260 600 2.0	mW mW/°C °C/W °C
Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25 $^{\circ}C$ Thermal Resistance, Junction to Ambient Junction and Storage Terr THERMAL CHARACTER Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25 $^{\circ}C$	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)	P _D R ₀ JA T _J , T _{stg}	-55 to +150 200 300 1.6 2.4 600 400 -55 to +150 260 600 2.0 4.8	mW mW/°C °C/W °C mW mW/°C

Table 2. THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBC143TF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 4) (Note 5) (Note 4) (Note 5)	P _D	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 4) (Note 5)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 4)	$R_{ heta JL}$	193	°C/W
Junction and Storage Tem	perature Range	T _J , T _{stg}	-55 to +150	°C

^{2.} FR-4 @ Minimum Pad.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	Ісво	_	-	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	_	-	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	-	-	1.9	mAdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)	V _(BR) CBO	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 6) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V _(BR) CEO	50	-	-	Vdc
ON CHARACTERISTICS		•			
DC Current Gain (Note 6) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	160	350	-	
Collector–Emitter Saturation Voltage (Note 6) (I _C = 10 mA, I _B = 1.0 mA)	V _{CE(sat)}	-	-	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A})$	$V_{i(off)}$	_	0.6	0.5	Vdc
Input Voltage (on) (V _{CE} = 0.3 V, I _C = 10 mA)	V _{i(on)}	1.3	0.9	-	Vdc
Output Voltage (on) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OL}	_	-	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.25 V, R _L = 1.0 k Ω)	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R ₁ /R ₂	-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

^{3.} FR-4 @ 1.0 x 1.0 Inch Pad.

^{4.} FR-4 @ 100 mm², 1 oz. copper traces, still air.
5. FR-4 @ 500 mm², 1 oz. copper traces, still air.

TYPICAL CHARACTERISTICS MUN2216, MMUN2216L, MUN5216, DTC143TM3

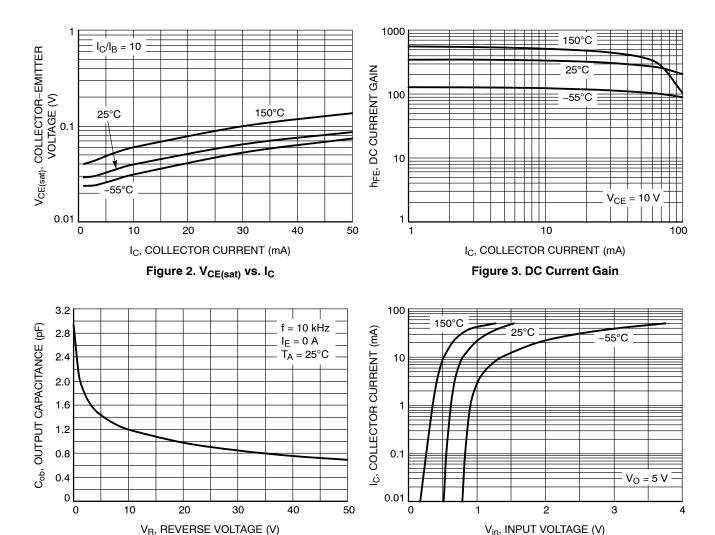


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

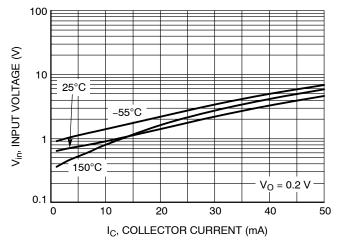


Figure 6. Input Voltage vs. Output Current

PACKAGE DIMENSIONS



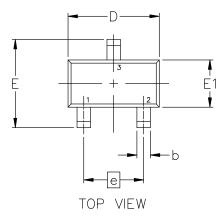
SC-59-3 2.90x1.50x1.15, 1.90P CASE 318D **ISSUE J**

DATE 15 FEB 2024

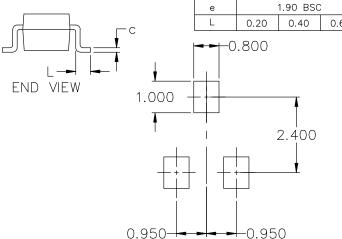
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

	MILLIMETERS			
DIM	MIN.	NOM.	MAX.	
Α	1.00	1.15	1.30	
A1	0.01	0.06	0.10	
b	0.35	0.43	0.50	
С	0.09	0.14	0.18	
D	2.70	2.90	3.10	
E	2.50	2.80	3.00	
E1	1.30	1.50	1.70	
е	1.90 BSC			
L	0.20	0.40	0.60	







RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.







XXX = Specific Device Code

= Date Code M

= Pb-Free Package*

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. ANODE PIN 1. ANODE 2. EMITTER 2. N.C. 3. CATHODE 3. CATHODE 3. COLLECTOR

STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. CATHODE STYLE 6: PIN 1. ANODE 2. CATHODE 2. CATHODE 2. N.C. 3. ANODE 3. ANODE/CATHODE



MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

PACKAGE DIMENSIONS



SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

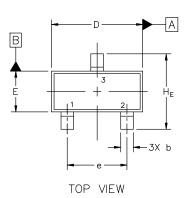
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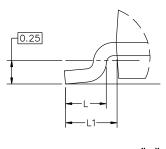
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0.69

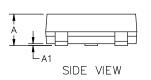
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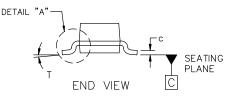
10°

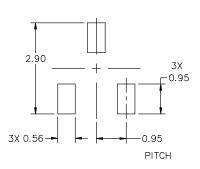




DETAIL "A" Scale 3:1







NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1.
- PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.3	0x1.00 1.90P	PAGE 1 OF 2	

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: STYLE 8: PIN 1. EMITTER PIN 1. ANOD 2. BASE 2. NO CC 3. COLLECTOR 3. CATHO	ONNECTION	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: STYLE 12: PIN 1. ANODE PIN 1. CATHO 2. CATHODE 2. CATHO 3. CATHODE-ANODE 3. ANODO	ODE 2. DRAIN 2. GATE	
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: STYLE 18: PIN 1. NO CONNECTION PIN 1. NO CO 2. ANODE 2. CATHO 3. CATHODE 3. ANODO	ODE 2. ANODE 2. ANODE	
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: STYLE 24: PIN 1. ANODE PIN 1. GATE 2. ANODE 2. DRAIN 3. CATHODE 3. SOURCE		CTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

DOCUMENT NUMBER:	98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.3	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	

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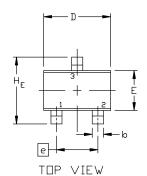


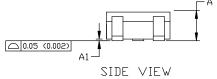
PACKAGE DIMENSIONS

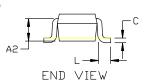


DATE 11 OCT 2022









NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



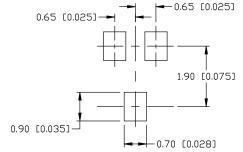


XX = Specific Device Code

М = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

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PACKAGE DIMENSIONS

SC75-3 1.60x0.80x0.80, 1.00P

CASE 463 ISSUE H

DATE 01 FEB 2024

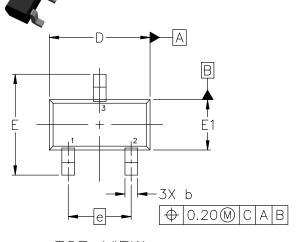
NOTES:

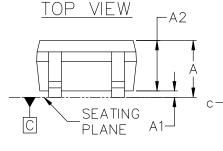
- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

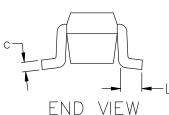
DIM	MILLIMETERS			
UIIVI	MIN.	NOM.	MAX.	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.10	
A2	0.80 REF.			
b	0.15	0.20	0.30	
С	0.10	0.15	0.25	
D	1.55	1.60	1.65	
Е	1.50	1.60	1.70	
E1	0.70	0.80	0.90	
е	1.00 BSC			
L	0.10	0.15	0.20	

-0.356

0.787







SIDE VIEW

GENERIC MARKING DIAGRAM*



XX = Specific Device Code Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. av ay

Pb-Free indicator, "G" or microdot "■", ma
or may not be present. Some products ma
not follow the Generic Marking.
-

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

RECOMMENDED MOUNTING FOOTPRINT* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

1.000

1.803

0.508

STYLE 4:
PIN 1. CATHODE
CATHODE
ANODE

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

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DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.0	00P	PAGE 1 OF 1	

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PACKAGE DIMENSIONS



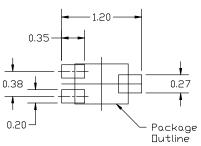
SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

DATE 18 JAN 2024

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS. 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

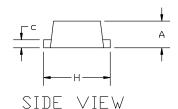
MILLIMETERS					
DIM	MIN	NDM	MAX		
Α	0.34	0.37	0.40		
b	0.15	0.22	0.28		
b1	0.10	0.15	0.20		
C	0.07	0.12	0.17		
D	0.75	0.80	0.85		
Е	0.55	0.60	0.65		
е	0.35	0.38	0.40		
Н	0.950	1.000	1.050		
L	0.185 REF				
L2	0.05	0.10	0.15		

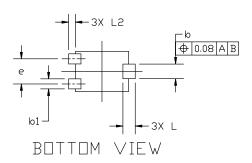


RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

В ТПР VIEW





GENERIC MARKING DIAGRAM*



= Specific Device Code

= Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
EMITTER
3 COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

STYLE 5: PIN 1. GATE 2. SOURCE

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1	

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PACKAGE DIMENSIONS



SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

DATE 24 JAN 2024

MAX.

0.55

0.27

0.37

0.17

1.25

0.85

1.25

0.25

MILLIMETERS

 $N\square M$.

0.50

0.21

0.31

0.12

1.20

0.80

0.40 BSC

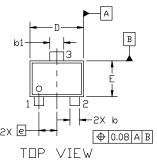
1.20

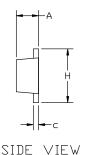
0.29 REF

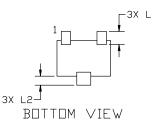
0.20

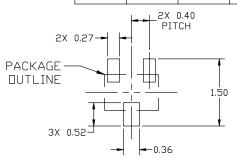
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.









DIM

Α

b

b1

 \subset D

Ε

е Н

L L2 MIN.

0.45

0.15

0.25

0.07

1.15

0.75

1.15

0.15

RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5: PIN 1. GATE 2. SOURCE PIN 1. BASE PIN 1. ANODE PIN 1. ANODE PIN 1. CATHODE 2 FMITTER 2 CATHODE 2 N/C 2. ANODE 3. COLLECTOR 3. CATHODE 3. CATHODE 3. DRAIN

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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1	

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